



# PMEG030V050EPD

30 V, 5 A low VF MEGA Schottky barrier rectifier

12 August 2016

Product data sheet

## 1. General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in a CFP15 (SOT1289) power and flat lead Surface-Mounted Device (SMD) plastic package.

## 2. Features and benefits

- Average forward current:  $I_{F(AV)} \leq 5$  A
- Reverse voltage:  $V_R \leq 30$  V
- Extremely low forward voltage
- High power capability due to clip-bonding technology and heat sink
- Small and thin SMD power plastic package, typical height 0.78 mm
- AEC-Q101 qualified

## 3. Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch mode power supply
- Freewheeling application
- Reverse polarity protection
- Low power consumption application

## 4. Quick reference data

Table 1. Quick reference data

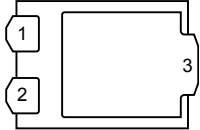
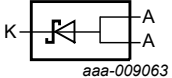
| Symbol      | Parameter               | Conditions   | Min | Typ | Max | Unit    |
|-------------|-------------------------|--|-----|-----|-----|---------|
| $I_{F(AV)}$ | average forward current | square wave; $\delta = 0.5$ ; $f = 20$ kHz;<br>$T_{sp} \leq 163$ °C        | -   | -   | 5   | A       |
| $V_R$       | reverse voltage         | $T_j = 25$ °C  | -   | -   | 30  | V       |
| $V_F$       | forward voltage         | $I_F = 5$ A; $t_p \leq 300$ $\mu$ s; $\delta \leq 0.02$ ;<br>$T_j = 25$ °C | -   | 440 | 500 | mV      |
| $I_R$       | reverse current         | $V_R = 10$ V; $T_j = 25$ °C; pulsed  | [1] | 9   | 30  | $\mu$ A |
|             |                         | $V_R = 30$ V; $T_j = 25$ °C; pulsed  | [1] | 45  | 150 | $\mu$ A |

[1] Very short test pulse to prevent junction self heating



## 5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline   | Graphic symbol  |
|-----|--------|-------------|--|---|
| 1   | A      | anode       |  <p>CFP15 (SOT1289)</p> |  <p>aaa-009063</p> |
| 2   | A      | anode       |  |   |
| 3   | K      | cathode     |  |   |

## 6. Ordering information

Table 3. Ordering information

| Type number    | Package |   |         |
|----------------|---------|---|---------|
|                | Name    | Description   | Version |
| PMEG030V050EPD | CFP15   | plastic, thermal enhanced ultra thin SMD package; 3 leads;<br>body: 5.8 x 4.3 x 0.78 mm | SOT1289 |

## 7. Marking

Table 4. Marking codes

| Type number    | Marking code |
|----------------|--------------|
| PMEG030V050EPD | 030V U05E    |

## 8. Limiting values

**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol      | Parameter                           | Conditions   |     | Min | Max  | Unit |
|-------------|-------------------------------------|--|-----|-----|------|------|
| $V_R$       | reverse voltage                     | $T_j = 25\text{ °C}$   |     | -   | 30   | V    |
| $I_F$       | forward current                     | $T_{sp} \leq 161\text{ °C}; \delta = 1$                                      |     | -   | 7    | A    |
| $I_{F(AV)}$ | average forward current             | square wave; $\delta = 0.5$ ; $f = 20\text{ kHz}; T_{sp} \leq 163\text{ °C}$ |     | -   | 5    | A    |
| $I_{FSM}$   | non-repetitive peak forward current | square wave; $t_p = 8\text{ ms}; T_{j(\text{init})} = 25\text{ °C}$          |     | -   | 120  | A    |
| $P_{tot}$   | total power dissipation             | $T_{amb} \leq 25\text{ °C}$  | [1] | -   | 1.66 | W    |
|             |                                     |  | [2] | -   | 2.15 | W    |
| $T_j$       | junction temperature                |  |     | -   | 175  | °C   |
| $T_{amb}$   | ambient temperature                 |  |     | -55 | 175  | °C   |
| $T_{stg}$   | storage temperature                 |  |     | -65 | 175  | °C   |

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm<sup>2</sup>.

## 9. Thermal characteristics

**Table 6. Thermal characteristics**

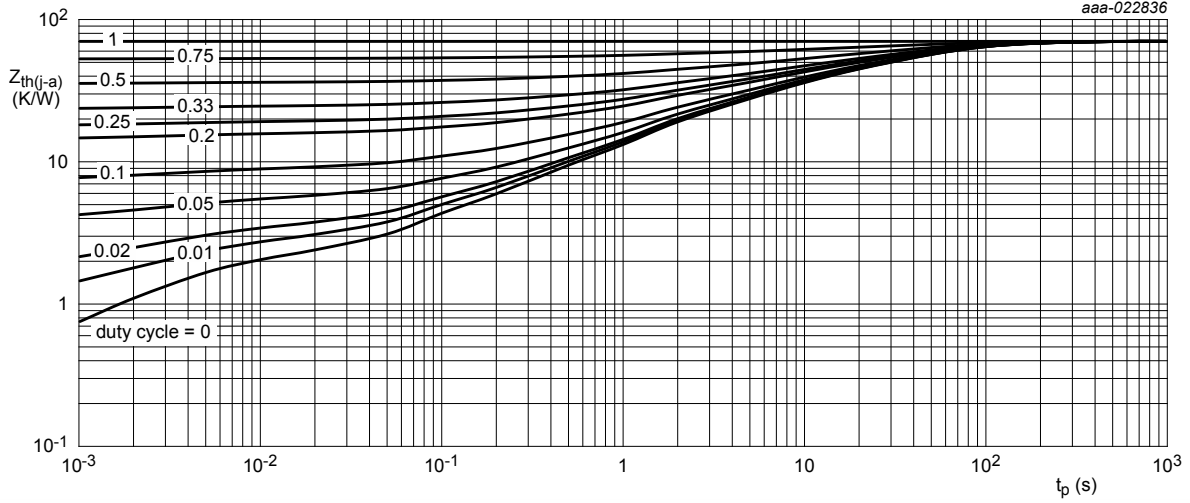
| Symbol         | Parameter  | Conditions  |        | Min | Typ | Max | Unit |
|----------------|--|-------------|--------|-----|-----|-----|------|
| $R_{th(j-a)}$  | thermal resistance from junction to ambient      | in free air | [1][2] | -   | -   | 90  | K/W  |
|                |  |             | [1][3] | -   | -   | 70  | K/W  |
| $R_{th(j-sp)}$ | thermal resistance from junction to solder point |             | [4]    | -   | -   | 3   | K/W  |

[1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses  $P_R$  are a significant part of the total power losses.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

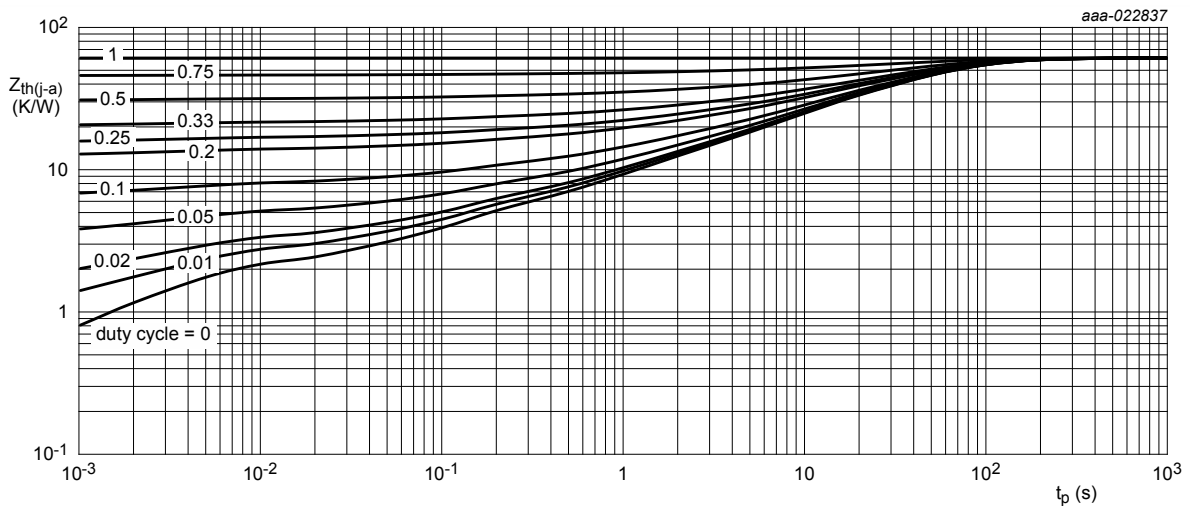
[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm<sup>2</sup>.

[4] Soldering point of cathode tab.



FR4 PCB, standard footprint

Fig. 1. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for cathode 1 cm<sup>2</sup>

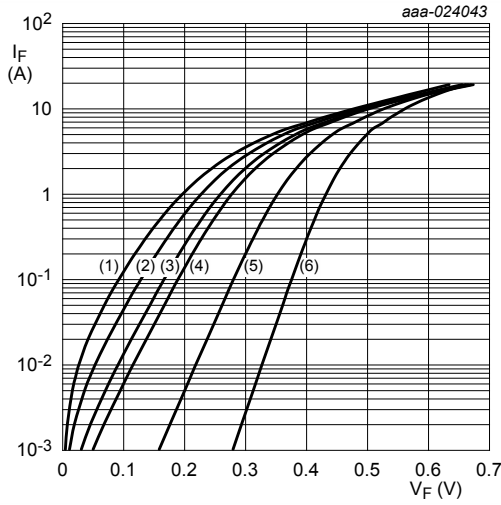
Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

## 10. Characteristics

Table 7. Characteristics

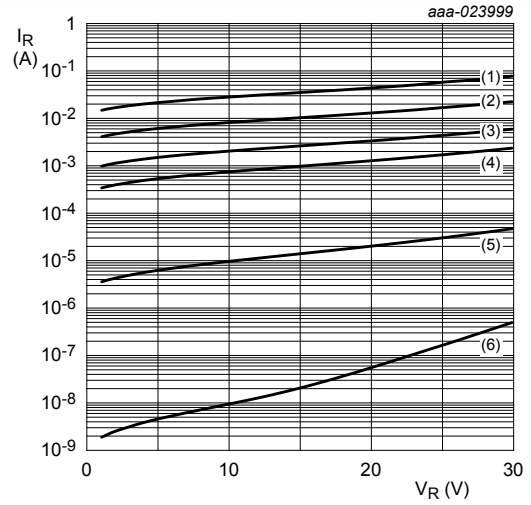
| Symbol      | Parameter                           | Conditions  |     | Min | Typ | Max | Unit          |
|-------------|-------------------------------------|---|-----|-----|-----|-----|---------------|
| $V_{(BR)R}$ | reverse breakdown voltage           | $I_R = 3 \text{ mA}; T_j = 25 \text{ }^\circ\text{C}; \text{ pulsed}$   | [1] | 30  | -   | -   | V             |
| $V_F$       | forward voltage                     | $I_F = 0.1 \text{ A}; t_p \leq 300 \text{ } \mu\text{s}; \delta \leq 0.02 ; T_j = 25 \text{ }^\circ\text{C}$    |     | -   | 280 | 320 | mV            |
|             |                                     | $I_F = 1 \text{ A}; t_p \leq 300 \text{ } \mu\text{s}; \delta \leq 0.02 ; T_j = 25 \text{ }^\circ\text{C}$      |     | -   | 350 | 400 | mV            |
|             |                                     | $I_F = 1.5 \text{ A}; t_p \leq 300 \text{ } \mu\text{s}; \delta \leq 0.02 ; T_j = 25 \text{ }^\circ\text{C}$    |     | -   | 365 | 420 | mV            |
|             |                                     | $I_F = 2 \text{ A}; t_p \leq 300 \text{ } \mu\text{s}; \delta \leq 0.02 ; T_j = 25 \text{ }^\circ\text{C}$      |     | -   | 380 | 440 | mV            |
|             |                                     | $I_F = 3 \text{ A}; t_p \leq 300 \text{ } \mu\text{s}; \delta \leq 0.02 ; T_j = 25 \text{ }^\circ\text{C}$      |     | -   | 400 | 450 | mV            |
|             |                                     | $I_F = 5 \text{ A}; t_p \leq 300 \text{ } \mu\text{s}; \delta \leq 0.02 ; T_j = 25 \text{ }^\circ\text{C}$      |     | -   | 440 | 500 | mV            |
|             |                                     | $I_F = 5 \text{ A}; t_p \leq 300 \text{ } \mu\text{s}; \delta \leq 0.02 ; T_j = -40 \text{ }^\circ\text{C}$     |     | -   | 500 | -   | mV            |
|             |                                     | $I_F = 5 \text{ A}; t_p \leq 300 \text{ } \mu\text{s}; \delta \leq 0.02 ; T_j = 125 \text{ }^\circ\text{C}$     |     | -   | 360 | -   | mV            |
| $I_R$       | reverse current                     | $V_R = 5 \text{ V}; T_j = 25 \text{ }^\circ\text{C}; \text{ pulsed}$  | [1] | -   | 6   | 15  | $\mu\text{A}$ |
|             |                                     | $V_R = 10 \text{ V}; T_j = 25 \text{ }^\circ\text{C}; \text{ pulsed}$   | [1] | -   | 9   | 30  | $\mu\text{A}$ |
|             |                                     | $V_R = 30 \text{ V}; T_j = 25 \text{ }^\circ\text{C}; \text{ pulsed}$   | [1] | -   | 45  | 150 | $\mu\text{A}$ |
|             |                                     | $V_R = 30 \text{ V}; T_j = 125 \text{ }^\circ\text{C}; \text{ pulsed}$  | [1] | -   | 22  | -   | mA            |
| $C_d$       | diode capacitance                   | $V_R = 1 \text{ V}; f = 1 \text{ MHz}; T_j = 25 \text{ }^\circ\text{C}$   |     | -   | 495 | -   | pF            |
|             |                                     | $V_R = 4 \text{ V}; f = 1 \text{ MHz}; T_j = 25 \text{ }^\circ\text{C}$   |     | -   | 265 | -   | pF            |
|             |                                     | $V_R = 10 \text{ V}; f = 1 \text{ MHz}; T_j = 25 \text{ }^\circ\text{C}$  |     | -   | 165 | -   | pF            |
| $t_{rr}$    | reverse recovery time step recovery | $I_F = 0.5 \text{ A}; I_R = 0.5 \text{ A}; I_{R(\text{meas})} = 0.1 \text{ A}; T_j = 25 \text{ }^\circ\text{C}$ |     | -   | 16  | -   | ns            |
|             | reverse recovery time ramp recovery | $dI_F/dt = 200 \text{ A}/\mu\text{s}; T_j = 25 \text{ }^\circ\text{C}; I_F = 6 \text{ A}; V_R = 26 \text{ V}$   |     | -   | 12  | -   | ns            |

[1] Very short test pulse to prevent junction self heating



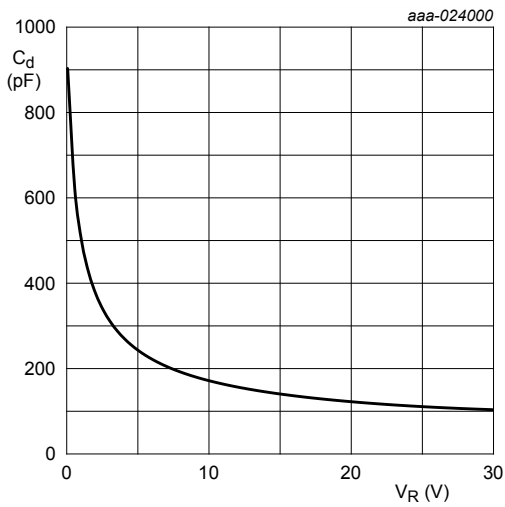
pulsed condition  
 (1)  $T_j = 150\text{ }^\circ\text{C}$   
 (2)  $T_j = 125\text{ }^\circ\text{C}$   
 (3)  $T_j = 100\text{ }^\circ\text{C}$   
 (4)  $T_j = 85\text{ }^\circ\text{C}$   
 (5)  $T_j = 25\text{ }^\circ\text{C}$   
 (6)  $T_j = -40\text{ }^\circ\text{C}$

**Fig. 3. Forward current as a function of forward voltage; typical values**



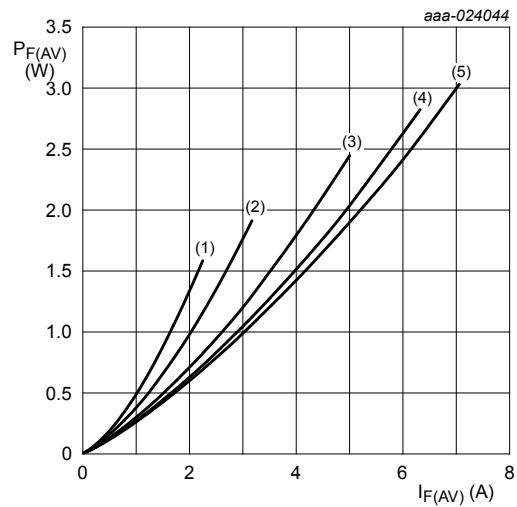
pulsed condition  
 (1)  $T_j = 150\text{ }^\circ\text{C}$   
 (2)  $T_j = 125\text{ }^\circ\text{C}$   
 (3)  $T_j = 100\text{ }^\circ\text{C}$   
 (4)  $T_j = 85\text{ }^\circ\text{C}$   
 (5)  $T_j = 25\text{ }^\circ\text{C}$   
 (6)  $T_j = -40\text{ }^\circ\text{C}$

**Fig. 4. Reverse current as a function of reverse voltage; typical values**



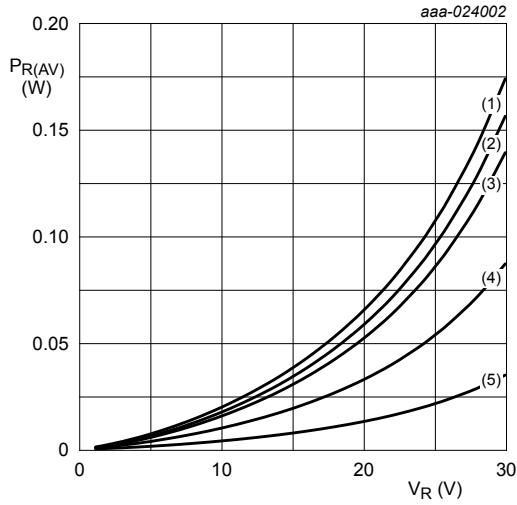
$f = 1\text{ MHz}; T_{amb} = 25\text{ }^\circ\text{C}$

**Fig. 5. Diode capacitance as a function of reverse voltage; typical values**



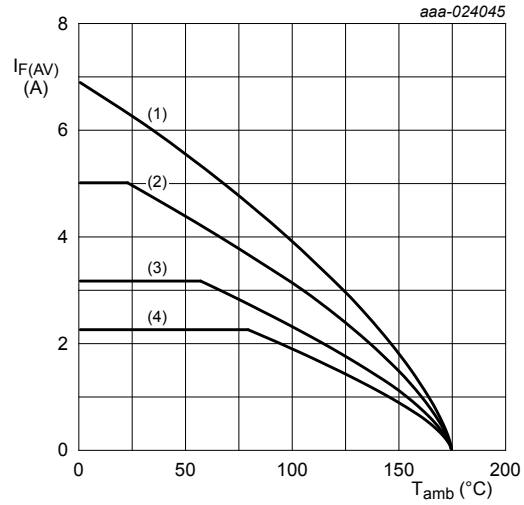
$T_j = 100\text{ }^\circ\text{C}$   
 (1)  $\delta = 0.1$   
 (2)  $\delta = 0.2$   
 (3)  $\delta = 0.5$   
 (4)  $\delta = 0.8$   
 (5)  $\delta = 1$

**Fig. 6. Average forward power dissipation as a function of average forward current; typical values**



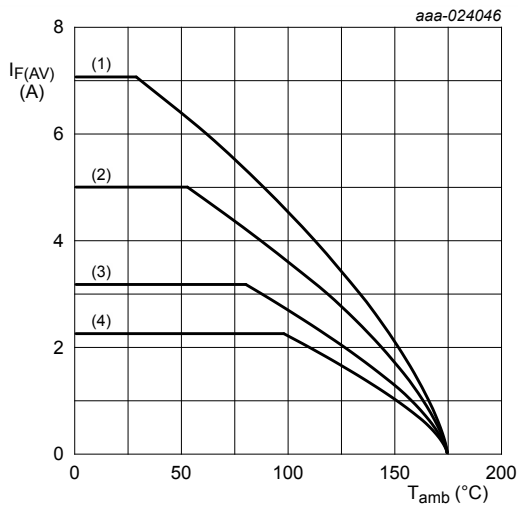
$T_j = 100\text{ }^\circ\text{C}$   
 (1)  $\delta = 1$   
 (2)  $\delta = 0.9$   
 (3)  $\delta = 0.8$   
 (4)  $\delta = 0.5$   
 (5)  $\delta = 0.2$

**Fig. 7. Average reverse power dissipation as a function of reverse voltage; typical values**



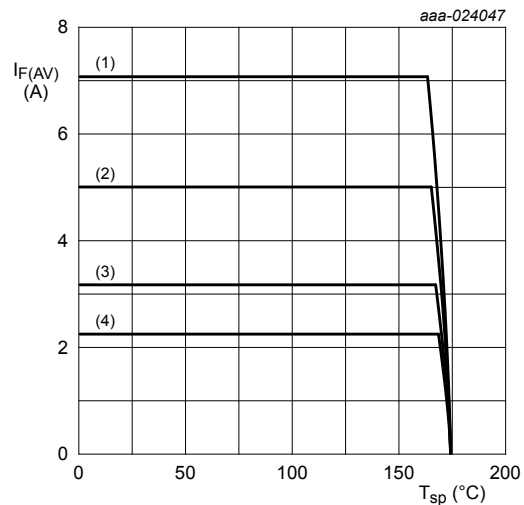
FR4 PCB, standard footprint  
 $T_j = 175\text{ }^\circ\text{C}$   
 (1)  $\delta = 1$ ; DC  
 (2)  $\delta = 0.5$ ;  $f = 20\text{ kHz}$   
 (3)  $\delta = 0.2$ ;  $f = 20\text{ kHz}$   
 (4)  $\delta = 0.1$ ;  $f = 20\text{ kHz}$

**Fig. 8. Average forward current as a function of ambient temperature; typical values**



FR4 PCB, mounting pad for cathode  $1\text{ cm}^2$   
 $T_j = 175\text{ }^\circ\text{C}$   
 (1)  $\delta = 1$ ; DC  
 (2)  $\delta = 0.5$ ;  $f = 20\text{ kHz}$   
 (3)  $\delta = 0.2$ ;  $f = 20\text{ kHz}$   
 (4)  $\delta = 0.1$ ;  $f = 20\text{ kHz}$

**Fig. 9. Average forward current as a function of ambient temperature; typical values**



$T_j = 175\text{ }^\circ\text{C}$   
 (1)  $\delta = 1$ ; DC  
 (2)  $\delta = 0.5$ ;  $f = 20\text{ kHz}$   
 (3)  $\delta = 0.2$ ;  $f = 20\text{ kHz}$   
 (4)  $\delta = 0.1$ ;  $f = 20\text{ kHz}$

**Fig. 10. Average forward current as a function of solder point temperature; typical values**

### 11. Test information

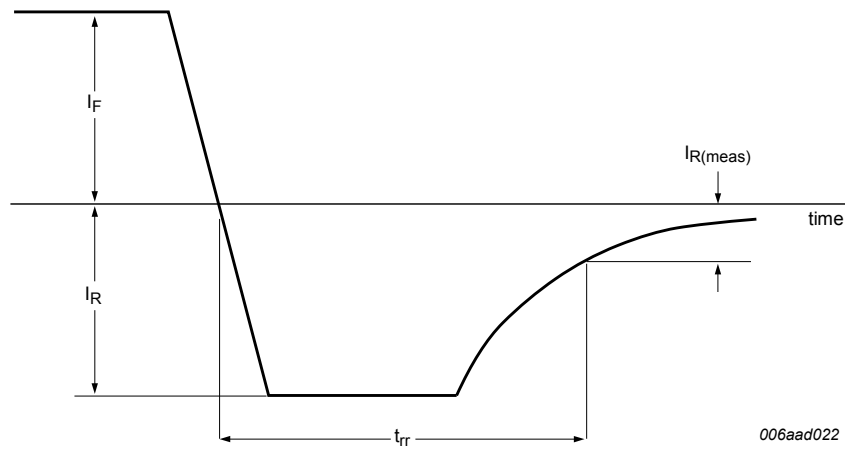


Fig. 11. Reverse recovery definition; step recovery

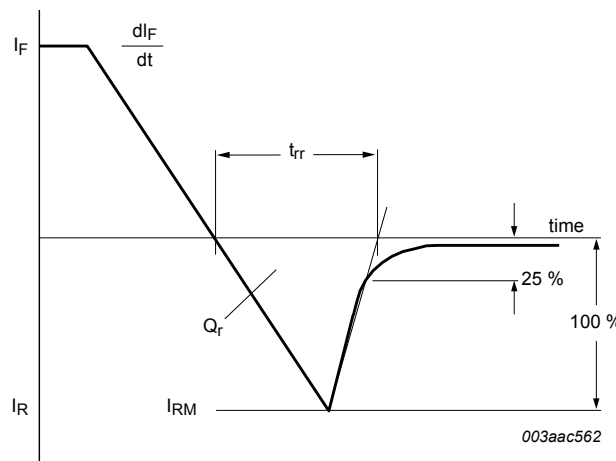


Fig. 12. Reverse recovery definition; ramp recovery

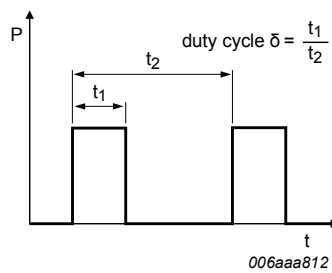


Fig. 13. Duty cycle definition

The current ratings for the typical waveforms are calculated according to the equations:  $I_{F(AV)} = I_M \times \delta$  with  $I_M$  defined as peak current,  $I_{RMS} = I_{F(AV)}$  at DC, and  $I_{RMS} = I_M \times \sqrt{\delta}$  with  $I_{RMS}$  defined as RMS current.



**Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

**12. Package outline**

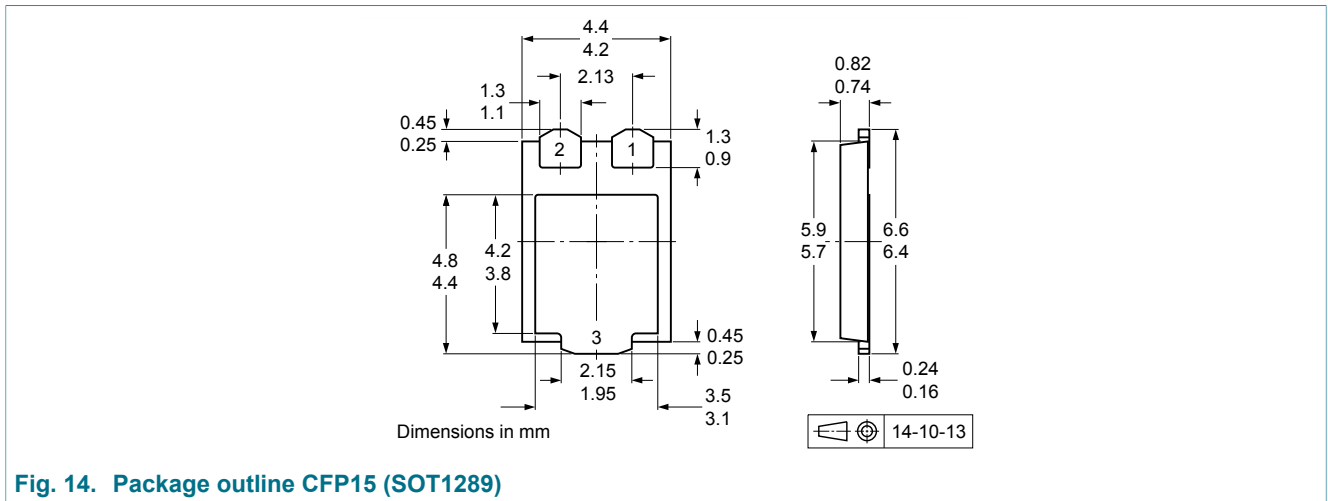


Fig. 14. Package outline CFP15 (SOT1289)

**13. Soldering**

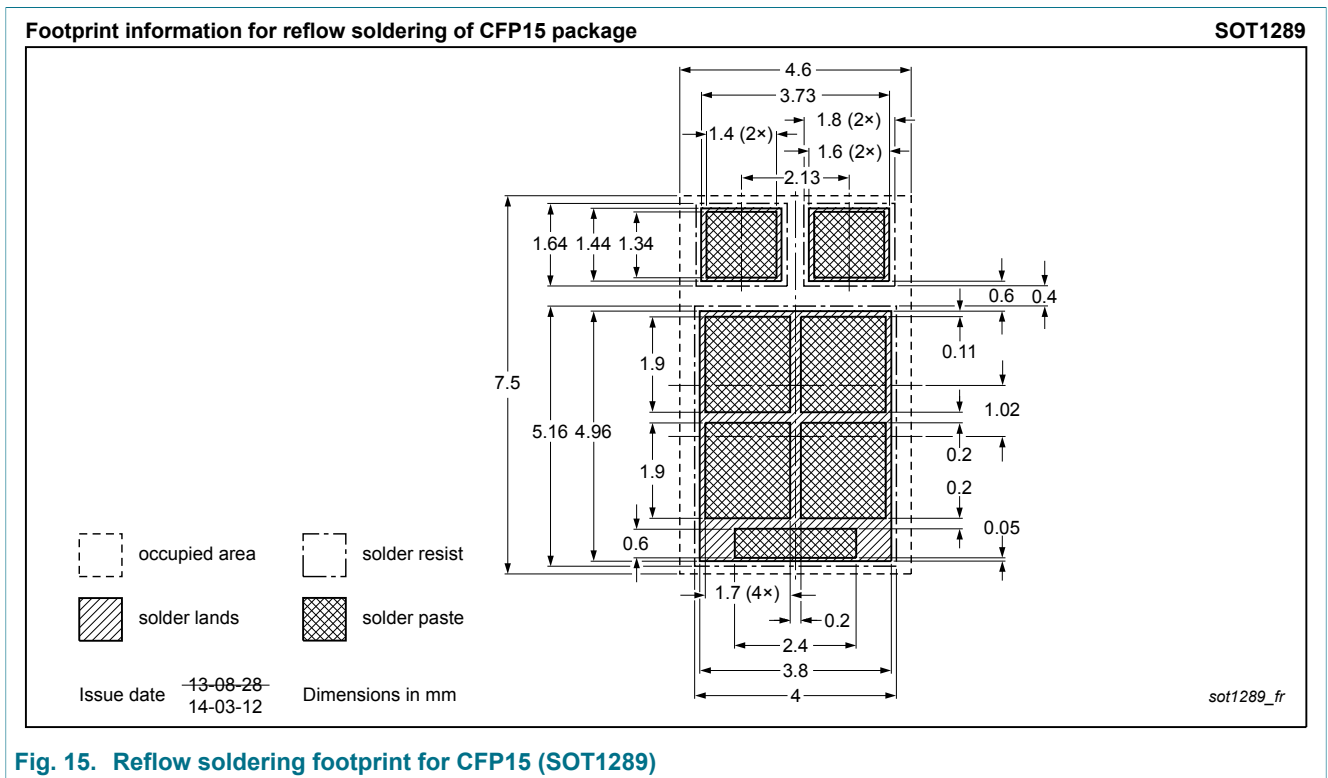


Fig. 15. Reflow soldering footprint for CFP15 (SOT1289)

## 14. Revision history

Table 8. Revision history

| Data sheet ID      | Release date | Data sheet status  | Change notice | Supersedes |
|--------------------|--------------|--------------------|---------------|------------|
| PMEG030V050EPD v.1 | 20160812     | Product data sheet | -             | -          |

## 15. Legal information

### Data sheet status

| Document status [1][2]         | Product status [3] | Definition  |
|--------------------------------|--------------------|---|
| Objective [short] data sheet   | Development        | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification      | This document contains data from the preliminary specification.                       |
| Product [short] data sheet     | Production         | This document contains the product specification.                                     |

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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Date of release: 12 August 2016

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